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STGB6NC60H

N-channel 600V - 7A - D²PAK Very fast PowerMESH™ IGBT

General features

Туре	V _{CES}	V _{CE(sat)} max @25°C	I _C @100°C
STGB6NC60H	600V	<2.5V	7A

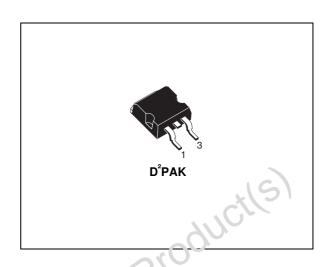
- Low on voltage drop (V_{cesat})
- Low C_{RES} / C_{IES} ratio (no cross-conduction susceptibility)
- Very soft ultra fast recovery antiparallel diode
- High frequency operation

Description

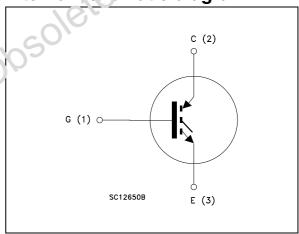
Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advaced family of IGBTs, the PowerMESHTM IGBTs, with outstanding performances. The suffix "H" identifies a family optimized for high frequency application in order to achieve very high switching performances (reduced tfall) mantaining a low voltage drop.

Applications

- High frequency inverters
- SMPS and PFC in bot'r nard switch and resonant topologies
- Motor drivers



Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STGB6NC60HT4	B6NC60HT4 GB6NC60H		Tape & reel

Contents STGB6NC60H

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STGB6NC60H Electrical ratings

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CES}	Collector-emitter voltage (V _{GS} = 0)	600	V
I _C ⁽¹⁾	Collector current (continuous) at T _C = 25°C	15	Α
I _C ⁽¹⁾	Collector current (continuous) at T _C = 100°C	7	Α
I _{CM} ⁽²⁾	Collector current (pulsed)	21	Α
V _{GE}	Gate-emitter voltage	±20	V
P _{TOT}	Total dissipation at T _C = 25°C	56	W
T _{stg}	Storage temperature	– 55 to 150	°C
T _j	Operating junction temperature	1(9	
T _I	Maximum lead temperature for soldering purpose (for 10sec. 1.6 mm from case)	300	°C

1. Calculated according to the iterative formula::

$$I_{C}(T_{C}) = \frac{T_{JMAX} - T_{C}}{R_{THJ} - C \times V_{CESAT(MAX)}(T_{C}, I_{C})}$$
on temperature

2. Pulse width limited by max junction temperature

Table 2. Thermal resistance

Symbol		Parameter	Value	Unit			
	Rthj-case	Thermal resistance junction-case max	2	°C/W			
	Rthj-amb	Thermal resistance junction-ambient max	62.5	°C/W			
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Electrical characteristics STGB6NC60H

2 Electrical characteristics

(T_{CASE}=25°C unless otherwise specified)

Table 3. Static

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{BR(CES)}	Collector-emitter breakdown voltage	I _C = 1mA, V _{GE} = 0	600			٧
V _{CE(sat)}	Collector-emitter saturation voltage	$V_{GE} = 15V, I_{C} = 3A$ $V_{GE} = 15V, I_{C} = 3A, T_{C} = 125^{\circ}C$		1.9 1.7	2.5	V V
V _{GE(th)}	Gate threshold voltage	$V_{CE} = V_{GE}, I_{C} = 250 \mu A$	3.75		5.75	V
I _{CES}	Collector cut-off current (V _{GE} = 0)	V_{CE} = Max rating, T_{C} = 25°C V_{CE} = Max rating, T_{C} = 125°C			10 1	μA mA
I _{GES}	Gate-emitter leakage current (V _{CE} = 0)	V _{GE} = ±20V , V _{CE} = 0		. (±100	nA
9 _{fs}	Forward transconductance	$V_{CE} = 15V_{,} I_{C} = 3A$		3		S

Table 4. Dynamic

	Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
	C _{ies} C _{oes} C _{res}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{CE} = 25V, f = 1MHz,$ $V_{GE} = 0$		205 32 5.5		pF pF pF
	Q _g Q _{ge} Q _{gc}	Total gate charge Gate-emitter charge Gate-collector charge	V_{CE} = 390V, I_{C} = 3A, V_{GE} = 15V, (see Figure 16)		13.6 3.4 5.1		nC nC nC
	I _{CL}	Turn-off SOA minimum current	V_{clamp} = 390V, Tj = 150°C, R_G = 10 Ω , V_{GE} = 15V		19		Α
Obsole	te P						

Table 5. Switching on/off (inductive load)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(on)}	Turn-on delay time	V _{CC} = 390V, I _C = 3A		12		ns
t _r	Current rise time	$R_{G} = 10\Omega$, $V_{GE} = 15V$,		5		ns
(di/dt) _{on}	Turn-on current slope	Tj = 25°C (see Figure 17)		612		A/µs
t _{d(on)}	Turn-on delay time	V _{CC} = 390V, I _C = 3A		13		ns
t _r	Current rise time	$R_G = 10\Omega, V_{GE} = 15V,$		4.3		ns
(di/dt) _{on}	Turn-on current slope	Tj =125°C (see Figure 17)		560		A/µs
t _r (V _{off})	Off voltage rise time	V _{CC} = 390V, I _C = 3A,		40		ns
$t_{d}(_{off})$	Turn-off delay time	$R_{GE} = 10\Omega$, $V_{GE} = 15V$,		76		ns
t _f	Current fall time	T _J = 25°C (see Figure 17)		100		ns
t _r (V _{off})	Off voltage rise time	$V_{CC} = 390V, I_C = 3A,$		60		ns
$t_{d}(_{off})$	Turn-off delay time	$R_{GE} = 10\Omega$, $V_{GE} = 15V$,		98		ns
t _f	Current fall time	Tj = 125°C (see Figure 17)		124	16	ns

Table 6. Switching energy (inductive load)

Symbol	Parameter	Test condictions	Min.	Тур.	Max.	Unit
E _{on} ⁽¹⁾ E _{off} ⁽²⁾ E _{ts}	Turn-on switching losses Turn-off switching losses Total switching losses	$V_{CC} = 390V$, $I_C = 3A$ $R_G = 10\Omega$, $V_{GE} = 15V$, $Tj = 25^{\circ}C$ (see Figure 17)		20 68 88		μJ μJ μJ
E _{on} ⁽¹⁾ E _{off} ⁽²⁾ E _{ts}	Turn-on switching losses Turn-off switching losses Total switching losses	V_{CC} = 390V, I_{C} = 3A R_{G} = 10 Ω V_{GE} = 15V, T_{J} = 125°C (see Figure 17)		37 93 130		μJ μJ μJ

Eon is the tun-on losses when a typical diode is used in the test circuit in figure 17. If the IGBT is offered in a package with a co-pak diode, the co-pack diode is used as external diode. IGBTs & Diode are at the same temperature (25°C and 125°C)

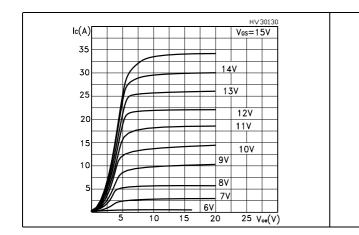
^{2.} Turn-off losses include also the tail of the collector current

Electrical characteristics STGB6NC60H

2.1 Electrical characteristics (curves)

Figure 1. Output characterisics

Figure 2. Transfer characteristics



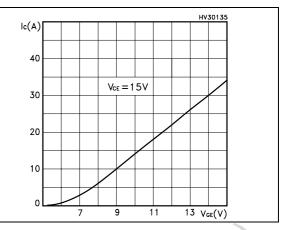
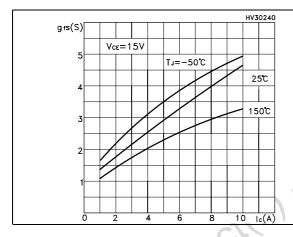


Figure 3. Transconductance

Figure 4. Collector-emitter on voltage vs temperature



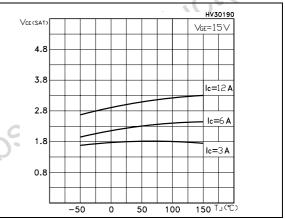
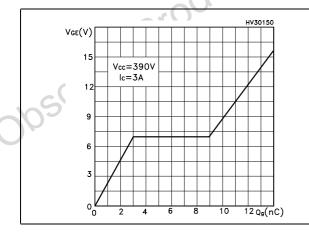


Figure 5. Gate charge vs gate-source voltage Figure 6. Capacitance variations



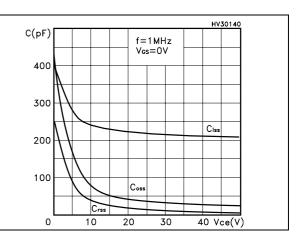


Figure 7. Normalized gate threshold voltage Figure 8. Collector-emitter on voltage vs vs temperature collector current

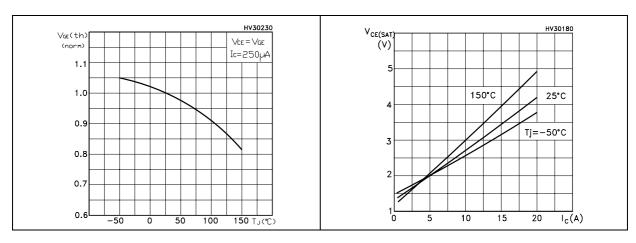


Figure 9. Normalized breakdown voltage vs Figure 10. Switching losses vs temperature temperature

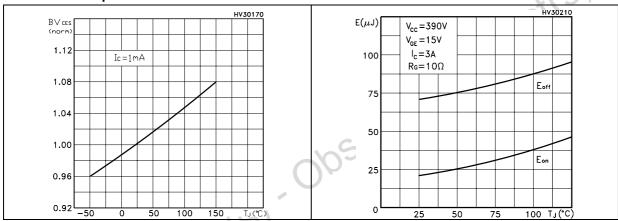
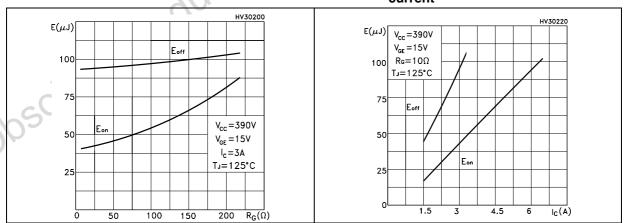


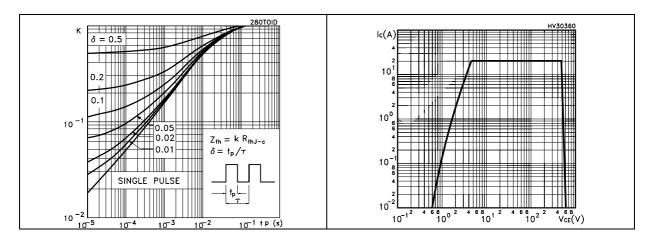
Figure 11. Switching losses vs gate resistance Figure 12. Switching losses vs collector current



Electrical characteristics STGB6NC60H

Figure 13. Thermal impedance

Figure 14. Turn-off SOA



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STGB6NC60H Test circuit

3 Test circuit

Figure 15. Test circuit for inductive load switching

Figure 16. Gate charge test circuit

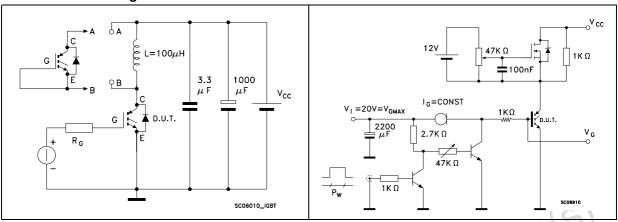
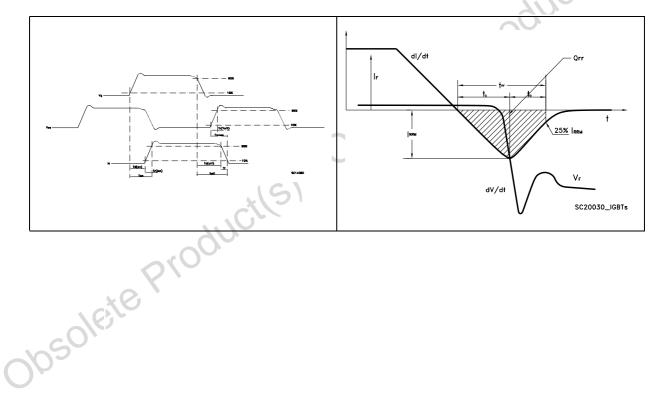


Figure 17. Switching waveform

Figure 18. Diode recovery time waveform



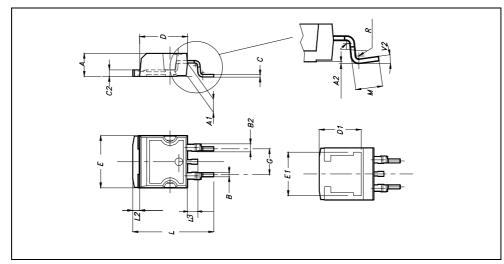
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

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D²PAK MECHANICAL DATA

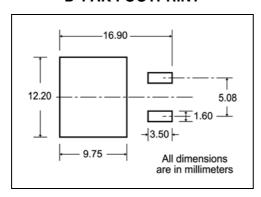
DIM.		mm.			inch	
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
Α	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
В	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
С	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
Е	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
М	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	O ₀		4º			



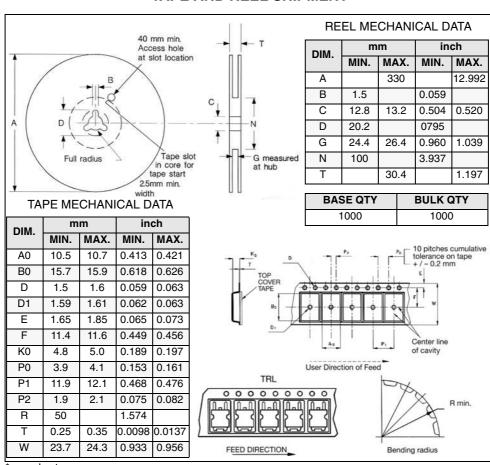
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5 Packaging mechanical data

D²PAK FOOTPRINT



TAPE AND REEL SHIPMENT







STGB6NC60H Revision history

6 Revision history

Table 7. Revision history

Date	Revision	Changes
18-Nov-2005	1	First Release
27-jul-2006	2	New template

Obsolete Product(s). Obsolete Product(s)

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